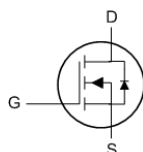
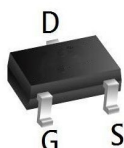


Description

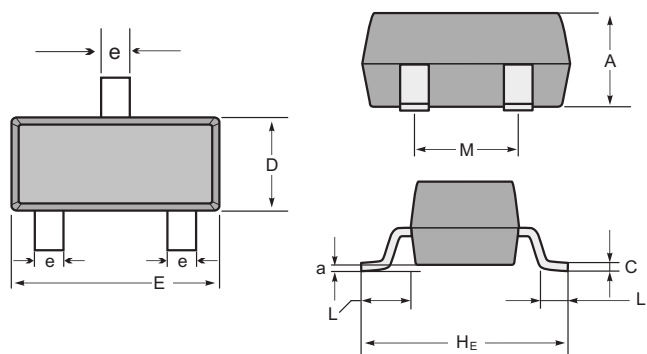
The 2N10 is the high cell density trench N-ch MOSFETs, which provides excellent RDS(on) and efficiency for most of the small power switching and load switch applications. The 1002C meet the RoHS and Green Product requirement with full function reliability approved.

Green Device Available
Super Low Gate Charge
Excellent Cdv/dt effect decline
Advanced high cell density Trench technology



Product Summary

BVDSS	RDS(on)	ID
100V	220mΩ	2A



SOT-23 mechanical data

UNIT		A	C	D	E	H _E	e	M	L	L ₁	a
mm	max	1.1	0.15	1.4	3.0	2.6	0.5	1.95	0.55 (ref)	0.36 (ref)	0.0
	min	0.9	0.08	1.2	2.8	2.2	0.3	1.7			0.15
mil	max	43	6	55	118	102	20	77	22 (ref)	14 (ref)	0.0
	min	35	3	47	110	87	12	67			6

Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Symbol	Parameter		Max.	Units
V _{DSS}	Drain-Source Voltage		100	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Continuous Drain Current	T _A = 25°C	2	A
		T _A = 100°C	1.4	A
I _{DM}	Pulsed Drain Current ^{note1}		8.8	A
P _D	Power Dissipation	T _A = 25°C	2.3	W
R _{θJA}	Thermal Resistance, Junction to Ambient		54	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C

2N10

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	100	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} =±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.2	V
R _{DS(on)}	Static Drain-Source on-Resistance note2	V _{GS} =10V, I _D =2A	-	220	286	mΩ
		V _{GS} =4.5V, I _D =1A	-	223	312	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, f=1.0MHz	-	321	-	pF
C _{oss}	Output Capacitance		-	21	-	pF
C _{rss}	Reverse Transfer Capacitance		-	15	-	pF
Q _g	Total Gate Charge	V _{DS} =30V, I _D =2A, V _{GS} =10V	-	5.3	-	nC
Q _{gs}	Gate-Source Charge		-	1.3	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	1.7	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DS} =30V, I _D =1A, R _{GEN} =3Ω, V _{GS} =10V	-	14	-	ns
t _r	Turn-on Rise Time		-	54	-	ns
t _{d(off)}	Turn-off Delay Time		-	18	-	ns
t _f	Turn-off Fall Time		-	11	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	2.2	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	8.8	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =2.2A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width≤300μs, Duty Cycle≤0.5%

RATING AND CHARACTERISTIC CURVES (2N10)

Figure1: Output Characteristics

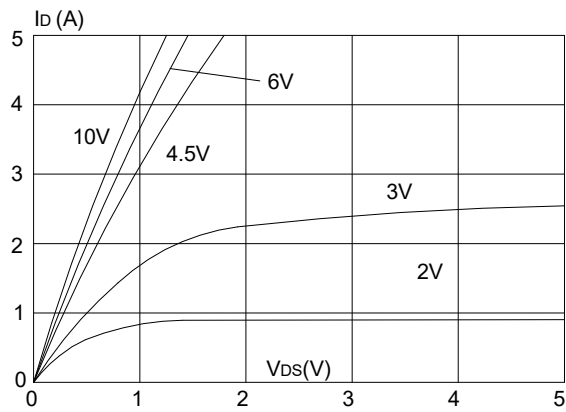


Figure 2: Typical Transfer Characteristics

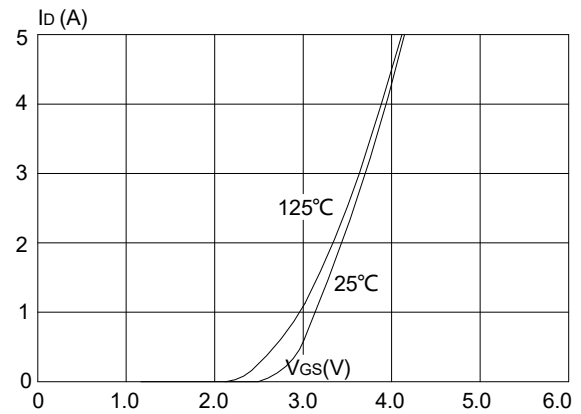


Figure 3: On-resistance vs. Drain Current

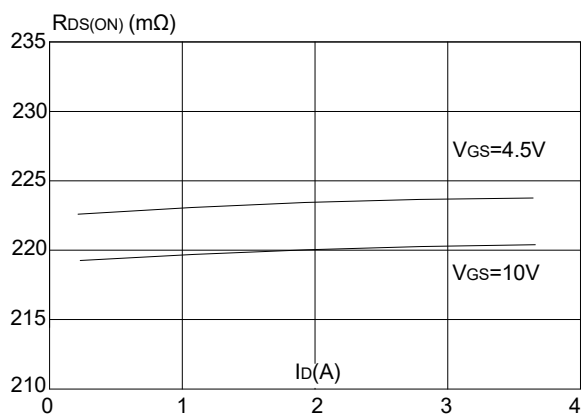


Figure 4: Body Diode Characteristics

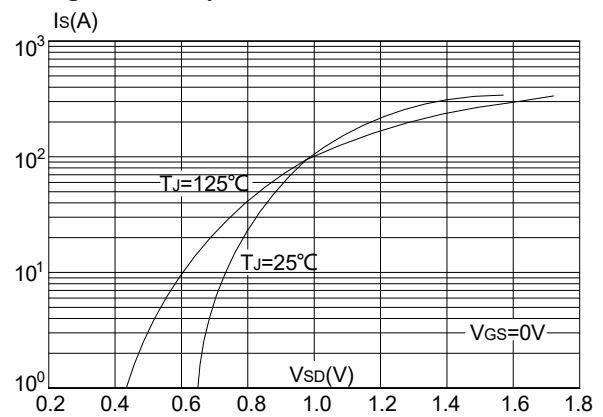


Figure 5: Gate Charge Characteristics

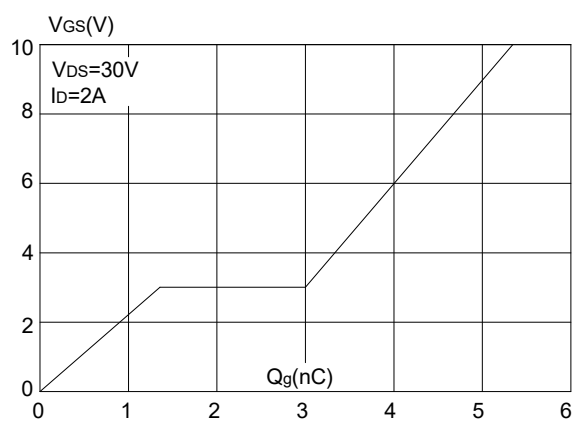
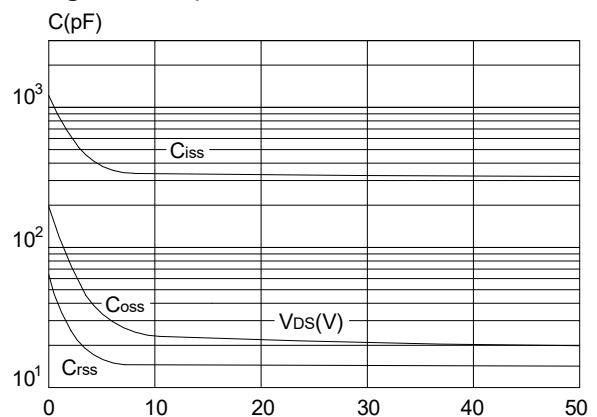


Figure 6: Capacitance Characteristics



RATING AND CHARACTERISTIC CURVES (2N10)

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

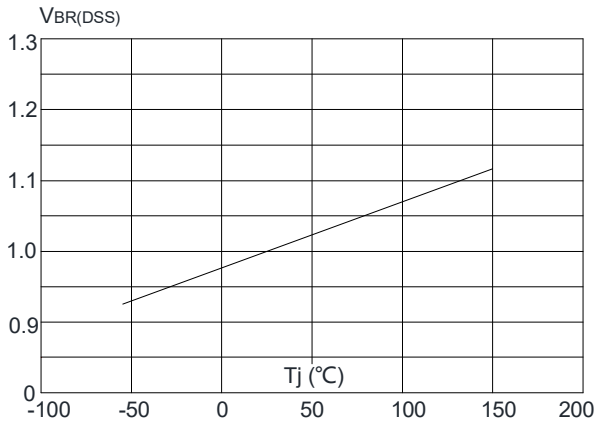


Figure 8: Normalized on Resistance vs. Junction Temperature

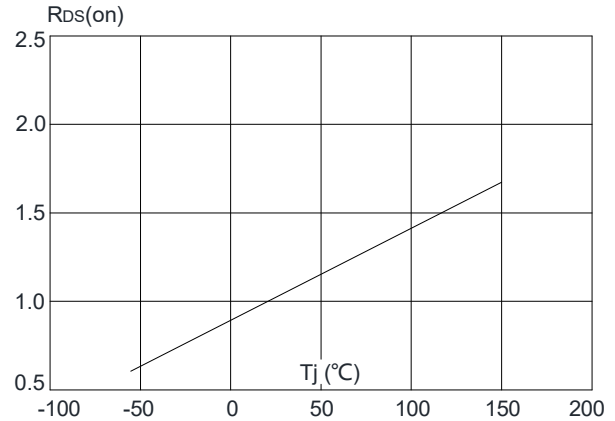


Figure 9: Maximum Safe Operating Area

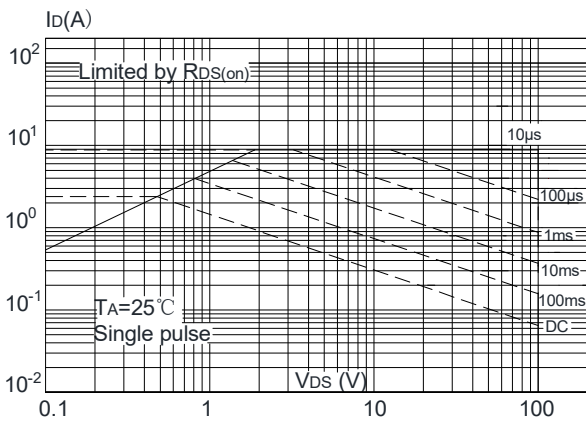


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

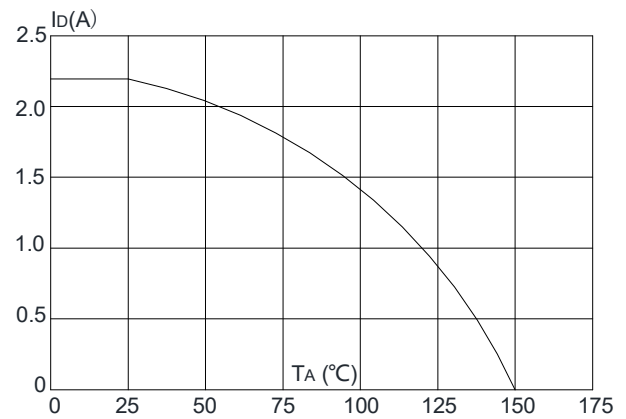


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

